

[illegible]

a MMIC;

a base plate that is matched as to its

5 coefficient of thermal expansion (CTE) with the MMIC;

a solder preform contained on the base plate,

said MMIC being mounted on the solder preform; and

a chip cover covering the MMIC, wherein the

base plate and chip cover are configured with

10 respective portions that engage each other and such

that any pads on said MMIC are exposed for wire and

ribbon bonding thereto, wherein the base plate and MMIC

are secured together by a solder flow process from said

solder preform.

25 microns

25 microns

25 microns

25 microns

[illegible]

10. A microwave monolithic integrated circuit (MMIC) package comprising:

- a MMIC;
- a substantially rectangular configured base plate that is matched as to its coefficient of thermal expansion (CTE) with the MMIC, said base plate including opposing side rails that extend along a portion of formed edges;
- a solder preform contained on the base plate, said MMIC being mounted on the solder preform; and
- a chip cover covering the MMIC, and secured on said side rails of said base plate, and having overlap legs extending down to said base plate, wherein the base plate, side rails, chip cover and overlap legs are configured such that any pads on said MMIC are exposed for wire and ribbon bonding thereto.

a chip cover covering the MMIC, and secured on said side rails of said base plate, and having overlap legs extending down to said base plate, wherein the base plate, side rails, chip cover and overlap legs
15 are configured such that any pads on said MMIC are exposed for wire and ribbon bonding thereto.

Sub #1
11. A microwave monolithic integrated circuit package according to Claim 10, wherein said base plate is formed from one of copper tungsten (CuW) or aluminum silicon (AlSi) alloy.

12. A microwave monolithic integrated circuit package according to Claim 10, wherein said base plate is about 10 to about 15 mil thick.

13. A microwave monolithic integrated circuit package according to Claim 10, wherein said solder preform is about 1 to about 2 mil thick.

14. A microwave monolithic integrated circuit package according to Claim 10, wherein said base plate and MMIC are secured together by a solder flow process with said solder preform.

15. A microwave monolithic integrated circuit package according to Claim 10, wherein said base plate and top cover are secured together by a solder flow process with said solder preform.

16. A method of forming a monolithic integrated circuit (MMIC) package comprising the steps of:

5 providing a base plate that is matched as to its coefficient of thermal expansion (CTE) with a MMIC to be packaged;

placing a solder preform onto the base plate;

placing a MMIC onto the solder preform;

10 placing a cover onto the MMIC to cover the chip, wherein the base plate and cover are configured such that any pads on the MMIC are exposed for wire and ribbon bonding thereto; and

heating to flow the solder
to the base plate.

17. A method according to
r comprising the step of heating
ic solder oven.

18. A method according to
r comprising the step of securing
ip cover to each other by a solder
er reflow process.

19. A method according to
r comprising the step of forming
ne of copper tungsten (CuW) or
alloy.

20. A method according to
r comprising the step of forming
10 to about 15 mil thick.

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